

## **isc Silicon NPN Power Transistors**

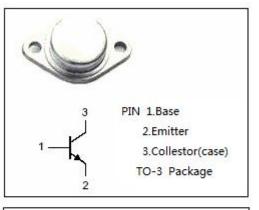
# BUY70C

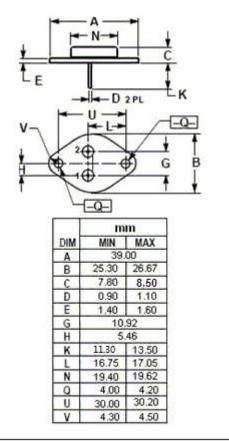
### DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V<sub>CEO(SUS)</sub> = 200V(Min)
- Low Collector-Emitter Saturation Voltage-: V<sub>CE(sat)</sub>= 5.0V(Max.)@ I<sub>C</sub>= 4A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for switching mode power supplies, inverters, and CRT scanning systems.





### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	200	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
Ic	Collector Current-Continuous	10	A
Ісм	Collector Current-peak	15	A
I <sub>B</sub>	Base Current-Continuous	3.0	A
Pc	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$		W
Tj	Junction Temperature	200	°C
T <sub>stg</sub>	Storage Temperature Range	-65~200	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.3	°C/W

isc website: <u>www.iscsemi.com</u>



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### ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	200			v
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	500			v
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	8			v
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			5.0	v
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			1.5	v
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V	15			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		6		MHz
Сов	Collector Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 20V			150	pF
t <sub>f</sub>	Fall Time	$I_{C}$ = 4A; $I_{B1}$ = - $I_{B2}$ = 0.8A; $V_{CC}$ = 40V			1.0	μ <b>s</b>

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